

NCEP85T25T

NCE N-Channel Super Trench Power MOSFET

Description

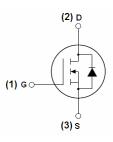
The NCEP85T25T uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =85V, I_{D} =250A $R_{DS(ON)}$ <2.8mΩ @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic diagram



TO-247 top view

100% UIS TESTED!

100% AVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP85T25T	NCEP85T25T	TO-247	-	-	-

Absolute Maximum Ratings (T_c=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	85	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	250	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	180	Α
Pulsed Drain Current	I _{DM}	800	Α
Maximum Power Dissipation	P _D	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1700	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R ₀ JC	0.5	°C/W
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NCEP85T25T

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA			-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V	_{DS} =85V,V _{GS} =0V -		1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	_S =0V -		±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =100A	-	-	2.8	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =100A	-	90	-	S
Dynamic Characteristics (Note4)	· ·		•	1		
Input Capacitance	C _{lss}	\/ -40\/\/ -0\/	-	11500	-	PF
Output Capacitance	Coss	V_{DS} =40V, V_{GS} =0V, F=1.0MHz	-	2990	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIFIZ	-	105	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	28	-	nS
Turn-on Rise Time	t _r	V_{DD} =40 V , I_{D} =100 A	-	73	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	86	-	nS
Turn-Off Fall Time	t _f		-	33	-	nS
Total Gate Charge	Q_g	\/ -40\/ L -400A	-	165		nC
Gate-Source Charge	Q _{gs}	V_{DS} =40V, I_{D} =100A, V_{GS} =10V	-	56		nC
Gate-Drain Charge	Q_{gd}	V _{GS} -10V	-	35		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _F = I _S	-		1.2	V
Diode Forward Current (Note 2)	Is	-		-	250	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	115		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	320		nC

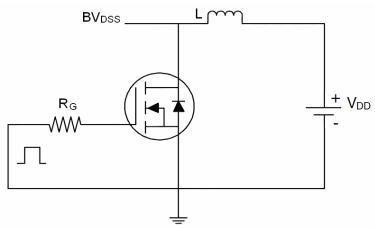
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{DD}$ =42.5V ,V $_{G}$ =10V ,L=0.5mH ,Rg=25 Ω

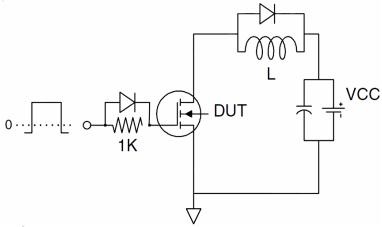


Test Circuit

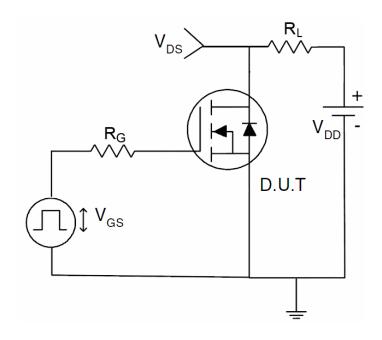
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit







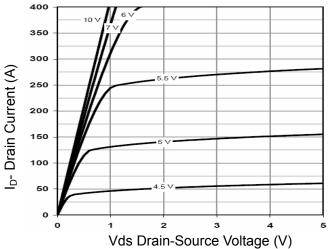


Figure 1 Output Characteristics

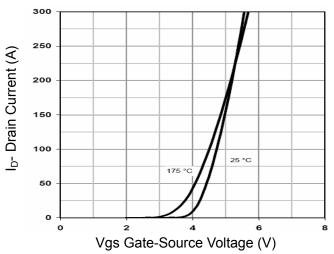


Figure 2 Transfer Characteristics

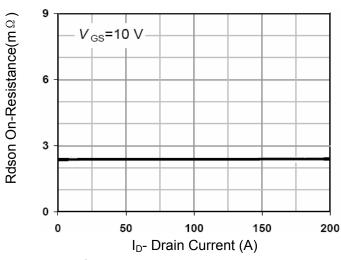


Figure 3 Rdson- Drain Current

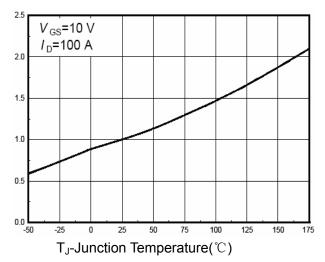


Figure 4 Rdson-JunctionTemperature

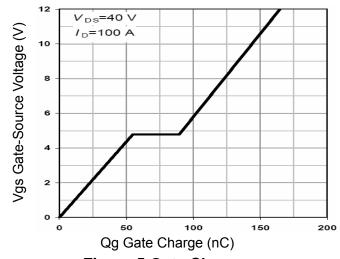


Figure 5 Gate Charge

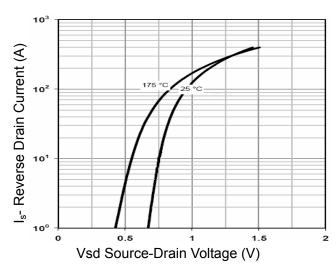


Figure 6 Source- Drain Diode Forward



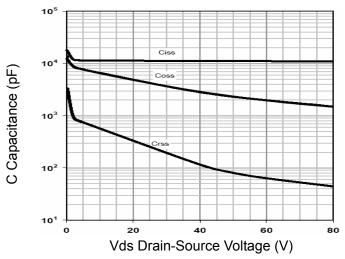


Figure 7 Capacitance vs Vds

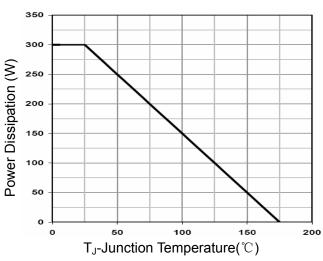


Figure 9 Power De-rating

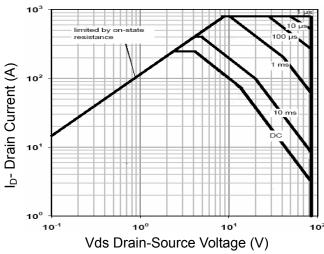


Figure 8 Safe Operation Area

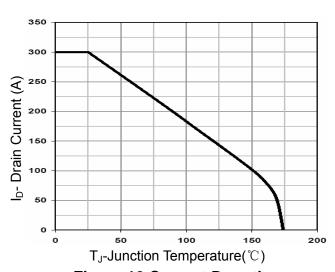


Figure 10 Current De-rating

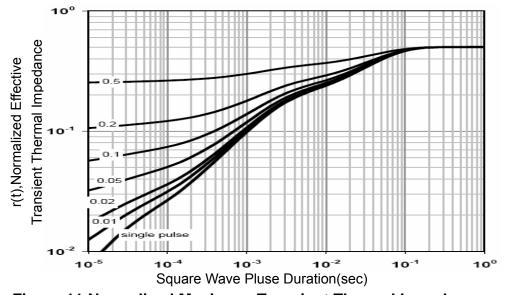


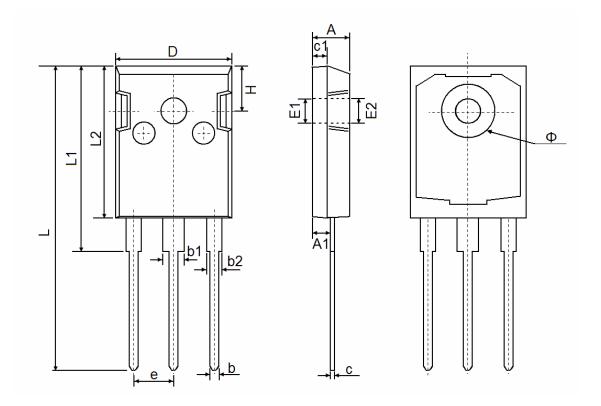
Figure 11 Normalized Maximum Transient Thermal Impedance

Pb Free Product



NCEP85T25T

TO-247 Package Information



Compleal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.850	5.150	0.191	0.200	
A1	2.200	2.600	0.087	0.102	
b	1.000	1.400	0.039	0.055	
b1	2.800	3.200	0.110	0.126	
b2	1.800	2.200	0.071	0.087	
С	0.500	0.700	0.020	0.028	
c1	1.900	2.100	0.075	0.083	
D	15.450	15.750	0.608	0.620	
E1	3.500) REF	0.138	REF	
E2	3.600) REF	0.142 REF		
L	40.900	41.300	1.610	1.626	
L1	24.800	25.100	0.976	0.988	
L2	20.300	20.600	0.799	0.811	
Ф	7.100	7.300	0.280	0.287	
е	5.450) TYP	0.215 TYP		
Н	5.980) REF	0.235 REF		



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